AMENDMENTS TO THE SPECIFICATION

Please amend the Abstract beginning on page 34 at line 2 as follows:

A method and system for use in monitoring/evaluating industrial processes such as, for example, plasma processes are provided. useful in the fabrication of semiconductor chips, microelectromechanical devices, and the like on semiconductor wafers and the like are provided. In one embodiment, a plasma process fault detection module (100) includes multiple sub-modulesa data selection sub-module (101), a model building/updating sub-module (102), a principal component analysis (PCA) analysis submodule (103), a model maintenance sub-module (104), a wafer categorization submodule (105), and a data output sub-module (106). The A data selection sub-module (101) obtains selected optical emissions spectra (OES) data for each wafer that is processed. The A model building/updating sub-module (102) constructs multiple models from the selected OES data for a number of wafers. The A principal component analysis (PCA) analysis sub-module (103) utilizes PCA techniques to determine whether the selected OES data for a particular wafer differs significantly from thatan expected for a normal wafer as represented by the models. The M model maintenance sub-module (104) saves and retrieves models for different processes, associating the current wafer with the correct process. The A wafer categorization sub-module (105) categorizes each wafer based on a scalar metric characterizing the residual spectrum vector. The A data output sub-module (106) outputs the results that are obtained to a user.